

FA01209

GaAs FET HYBRID IC

DESCRIPTION

FA01209 is RF Hybrid IC designed for 900MHz band small size hand held radio.

FEATURES

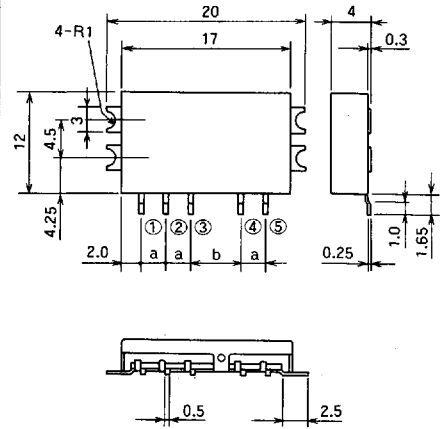
- High efficiency 35 (%)
- High power 31 (dBm)
- High gain 24 (dB)
- Small size 20×12×4 (mm)
- Frequency range 940~956 (MHz)

APPLICATION

Small size hand held radio for 900MHz band.

Modulation : $\pi/4$ DQPSK

OUTLINE DRAWING Dimensions in mm



Lead pitch : a=2.5
 b=5.0

- ① RF INPUT
- ② V_{G1,2}
- ③ V_{D1}
- ④ V_{D2}
- ⑤ RF OUTPUT
- fin : GND

GH-7

ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

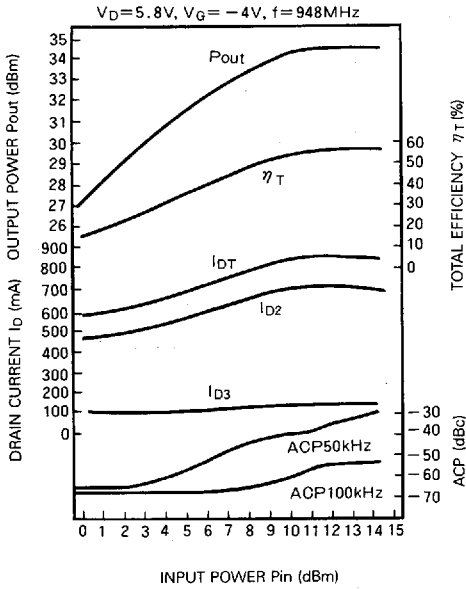
Symbol	Parameter	Rating	Unit
V _D	Supply voltage	9	V
V _G	Gate bias voltage	-5.5	V
I _{D1}	Drain current (1st stage)	400	mA
I _{D2}	Drain current (2nd stage)	900	mA
P _{in}	Input power	15	dBm
T _{C(OP)}	Operation case temperature	-20 ~ +85	°C
T _{stg}	Storage temperature	-30 ~ +90	°C

Each Maximum Rating is guaranteed independently and under pulse operation.

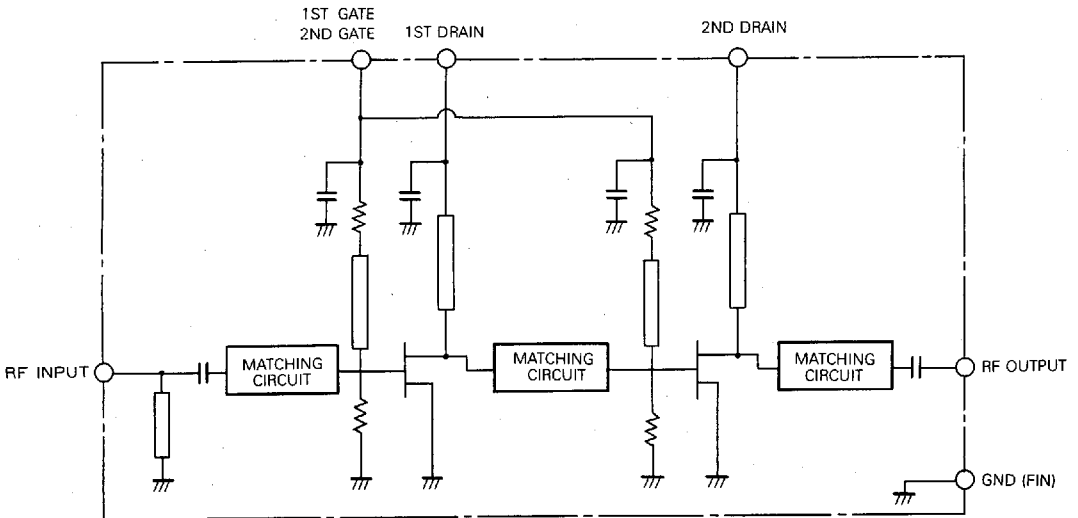
ELECTRICAL CHARACTERISTICS (Ta=25°C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
f	Frequency		940	—	956	MHz
P _{in}	Input power		—	7.0	10.0	dBm
η_T	Total efficiency		—	35	—	%
ρ_{in}	Input VSWR	P _O =31.0dBm	—	—	3 : 1	—
2f ₀	2nd harmonics	V _{D1} =V _{D2} =5.8V, V _{G1} =V _{G2} =-4.0V	—	—	-30	dBc
3f ₀	3rd harmonics	P _{in} : controlled, Z _G =Z _L =50Ω	—	—	-30	dBc
ACP ₅₀	±50kHz adjacent channel power		—	—	-46	dBc
ACP ₁₀₀	±100kHz adjacent channel power		—	—	-61	dBc

TYPICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)



EQUIVALENT CIRCUIT



M5M27C102P,FP,J,VP,RV-15

MITSUBISHI (MEMORY/ASIC)

**1048576-BIT(65536-WORD BY 16-BIT)
CMOS ONE TIME PROGRAMMABLE ROM**

T-46-13-25

FUNCTION**Read**

Set the \overline{CE} and \overline{OE} terminals to the read mode (low level). Low level input to \overline{CE} and \overline{OE} and address signals to the address inputs ($A_0 \sim A_{15}$) make the data contents of the designated address location available at the data input/output ($D_0 \sim D_{15}$). When the \overline{CE} or \overline{OE} signal is high, data input/output are in a floating state.

When the \overline{CE} signal is high, the device is in the standby mode or power-down mode.

Programming**(Word programming algorithm)**

The M5M27C102P, FP, J, VP, RV-15 enter the word programming mode when 12.5V is supplied to the V_{PP} power supply input, \overline{CE} is at low level and \overline{OE} is at high level. A location is designated by address signals ($A_0 \sim A_{15}$), and the data to be programmed must be applied at 16-bits in parallel to the data inputs ($D_0 \sim D_{15}$). In this state, word programming is completed when \overline{PGM} is at low level.

(Page programming algorithm)

Page programming feature of the M5M27C102P, FP, J, VP, RV-15 allows 2 words of data to be simultaneously programmed. The destination addresses for a page programming operation must reside on the same page; that is, A_1 through A_{15} must not change. At first, the M5M27C102P, FP, J, VP, RV-15 enter the page data latch mode when $V_{PP} = 12.5V$, $\overline{CE} = "H"$, $\overline{OE} = "L"$ and $\overline{PGM} = "H"$. A first and second locations in same page are designated by address signals ($A_0 \sim A_{15}$), and the data to be programmed must be applied to each location at 16-bits in parallel to the data inputs ($D_0 \sim D_{15}$). In this state, the data (2 words) latch is completed. Then the M5M27C102P, FP, J, VP, RV-15 enter the page programming mode when $\overline{OE} = "H"$. In this state, page (2 words) programming is completed when $\overline{PGM} = "L"$.

Erase

The M5M27C102P, FP, J, VP, RV-15 cannot be erased, because they are packaged in plastic without transparent lid.

MODE SELECTION

Mode	Pins	\overline{OE}	\overline{CE}	\overline{PGM}	V_{PP}	V_{CC}	Data I/O
Read		V_{IL}	V_{IL}	X*	5V	5V	Data out
Output disable		V_{IL}	V_{IH}	X*	5V	5V	Floating
Standby (Power down)		V_{IH}	X*	X*	5V	5V	Floating
Word program		V_{IL}	V_{IH}	V_{IL}	12.5V	6V	Data in
Program verify		V_{IL}	V_{IL}	V_{IH}	12.5V	6V	Data out
Page data latch		V_{IH}	V_{IL}	V_{IH}	12.5V	6V	Data in
Page program		V_{IH}	V_{IH}	V_{IL}	12.5V	6V	Floating
Program inhibit		V_{IL}	V_{IL}	V_{IL}	12.5V	6V	Floating
		V_{IL}	V_{IH}	V_{IH}	12.5V	6V	
		V_{IH}	V_{IL}	V_{IL}	12.5V	6V	
		V_{IH}	V_{IH}	V_{IH}	12.5V	6V	

* : X can be either V_{IL} or V_{IH} .

ABSOLUTE MAXIMUM RATINGS (Note 1)

Symbol	Parameter	Test condition	Rating	Unit
V_{I1}	All input or output voltage except $V_{PP} - A_9$	With respect to Ground	-0.6~7	V
V_{I2}	V_{PP} supply voltage		-0.6~14.0	V
V_{I3}	A_9 supply voltage		-0.6~13.5	V
T_{opr}	Operating temperature		-10~80	°C
T_{stg}	Storage temperature		-65~150	°C

Note 1: Stresses above those listed may cause permanent damage to the device. This is a stress rating only and functional operation of the device at those or at any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods affects device reliability.

M5M27C102P,FP,J,VP,RV-15

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READ OPERATION

DC ELECTRICAL CHARACTERISTICS ($T_a=0\sim 70^\circ\text{C}$, $V_{CC}=5V\pm 5\%$, $V_{PP}=V_{CC}$, unless otherwise noted)

Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
I_{LI}	Input load current	$V_{IN}=0V\sim V_{CC}$			10	μA
I_{LO}	Output leakage current	$V_{OUT}=0V\sim V_{CC}$			10	μA
I_{PP1}	V_{PP} current read	$V_{PP}=5.5V$		1	100	μA
I_{SB1}	V_{CC} current standby	$\overline{CE}=V_{IH}$			1	mA
I_{SB2}		$\overline{CE}=V_{CC}$		1	100	μA
I_{CO1}	V_{CC} current Active	$\overline{OE}=\overline{OE}=V_{IL}$			50	mA
I_{CO2}		$f=6.7\text{MHz}$, $I_{out}=0\text{mA}$			50	mA
V_{IL}	Input low voltage		-0.1		0.8	V
V_{IH}	Input high voltage		2.0		$V_{CC}+1$	V
V_{OL}	Output low voltage	$I_{OL}=2.1\text{mA}$			0.45	V
V_{OH}	Output high voltage	$I_{OH}=-400\mu\text{A}$	2.4			V

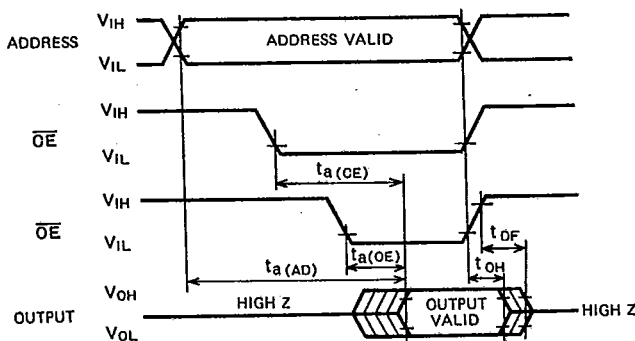
Note 2: Typical values are at $T_a = 25^\circ\text{C}$ and nominal supply voltages.

AC ELECTRICAL CHARACTERISTICS ($T_a=0\sim 70^\circ\text{C}$, $V_{CC}=5V\pm 5\%$, $V_{PP}=V_{CC}$, unless otherwise noted)

Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
$t_a(\text{AD})$	Address to output delay	$\overline{CE}=\overline{OE}=V_{IL}$			150	ns
$t_a(\overline{OE})$	\overline{CE} to output delay	$\overline{OE}=V_{IL}$			150	ns
$t_a(\overline{OE})$	Output enable to output delay	$\overline{OE}=V_{IL}$			60	ns
t_{DF}	Output enable high to output float	$\overline{OE}=V_{IL}$	0		50	ns
t_{OH}	Output hold from \overline{CE} , \overline{OE} or addresses		0			ns

Note 3: V_{CC} must be applied simultaneously V_{PP} and removed simultaneously V_{PP} .

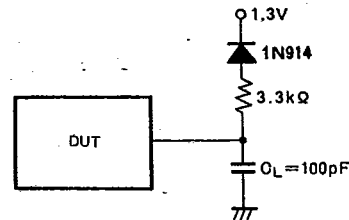
AC WAVEFORMS



Test conditions for A.C. characteristics
 Input voltage: $V_{IL} = 0.45V$, $V_{IH} = 2.4V$
 Input rise and fall times: $\leq 20\text{ns}$
 Reference voltage at timing measurement: Input, Output
 "L" = 0.8V, "H" = 2V.

Output load: 1TTL gate + C_L (100pF)

or



CAPACITANCE

Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
C_{IN}	Input capacitance (Address, \overline{CE} , \overline{OE} , FGM)	$T_a=25^\circ\text{C}$, $f=1\text{MHz}$, $V_1=V_0=0V$			15	pF
C_{OUT}	Output capacitance				15	pF

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PROGRAM OPERATION**WORD PROGRAMMING ALGORITHM**

First set $V_{CC} = 6V$, $V_{PP} = 12.5V$ and then set an address to first address to be programmed. After applying 0.2 ms program pulse (PGM) to the address, verify is performed. If the output data of that address is not verified correctly, apply one more 0.2 ms program pulse. The programmer continues 0.2 ms pulse-then-verify routines until the device verify correctly or twenty five of these pulse-then-verify routines have been completed. The programmer, also

maintains its total number of 0.2 ms pulse applied to that address in register X. And then applied a program pulse X times of 0.2 ms width as an overprogram pulse. When the programming procedure above is finished, step to the next address and repeat this procedure till last address to be programmed. When the entire addresses have been programmed completely, all addresses should be verified with $V_{CC} = V_{PP} = 5V$.

DC ELECTRICAL CHARACTERISTICS ($T_a = 25 \pm 5^\circ C$, $V_{CC} = 6V \pm 0.25V$, $V_{PP} = 12.5V \pm 0.3V$, unless otherwise noted)

Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
I_{LI}	Input current	$V_{IN} = 0V \sim V_{CC}$			10	μA
V_{OL}	Output low voltage	$I_{OL} = 2.1mA$			0.45	V
V_{OH}	Output high voltage	$I_{OH} = -400\mu A$	2.4			V
V_{IL}	Input low voltage		-0.1		0.8	V
V_{IH}	Input high voltage		2.0		V_{CC}	V
I_{CC}	V_{CC} supply current				50	mA
I_{PP}	V_{PP} supply current	$\overline{OE} = \overline{PGM} = V_{IL}$			50	mA

AC ELECTRICAL CHARACTERISTICS ($T_a = 25 \pm 5^\circ C$, $V_{CC} = 6V \pm 0.25V$, $V_{PP} = 12.5V \pm 0.3V$, unless otherwise noted)

Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
t_{AS}	Address setup time		2			μs
t_{OES}	\overline{OE} set up time		2			μs
t_{DS}	Data setup time		2			μs
t_{AH}	Address hold time		0			μs
t_{DH}	Data hold time		2			μs
t_{DFP}	Chip enable to output float delay		0		130	ns
t_{VOS}	V_{CC} setup time		2			μs
t_{VPS}	V_{PP} setup time		2			μs
t_{PW}	PGM initial program pulse width		0.19	0.2	0.21	ms
t_{OPW}	PGM over program pulse width		0.19		5.25	ms
t_{CES}	\overline{CE} setup time		2			μs
t_{OE}	Data valid from \overline{OE}				150	ns

Note 4: V_{CC} must be applied simultaneously V_{PP} and removed simultaneously V_{PP} .

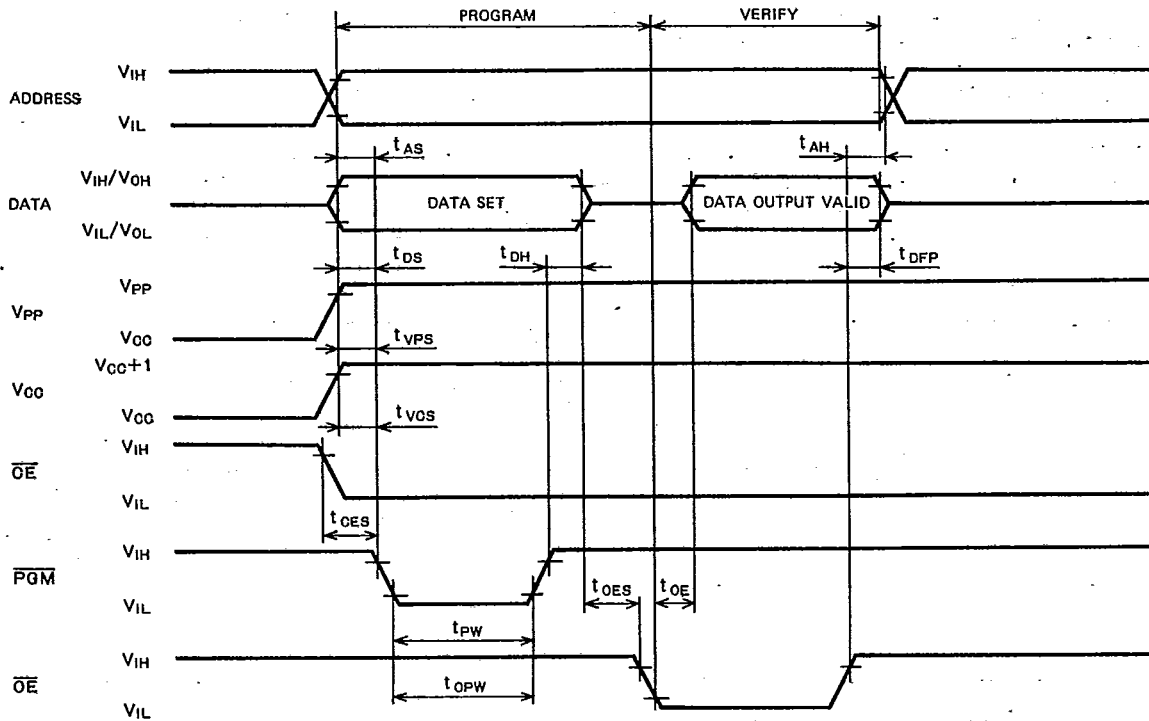
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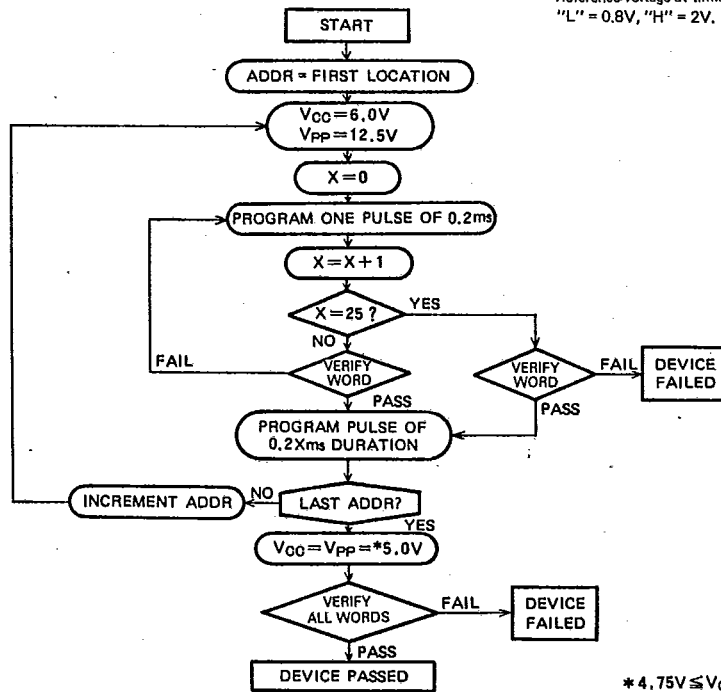
T-46-13-25

AC WAVEFORMS



Test conditions for A.C. characteristics
 Input voltage: $V_{IL} = 0.45V$, $V_{IH} = 2.4V$
 Input rise and fall times: $\leq 20ns$
 Reference voltage at timing measurement: Input, Output
 "L" = 0.8V, "H" = 2V.

WORD PROGRAMMING ALGORITHM FLOW CHART



* $4.75V \leq V_{CC} = V_{PP} \leq 5.25V$

M5M27C102P,FP,J,VP,RV-15

MITSUBISHI (MEMORY/ASIC)

**1048576-BIT(65536-WORD BY 16-BIT)
CMOS ONE TIME PROGRAMMABLE ROM****PAGE PROGRAMMING ALGORITHM**

T-46-13-25

First set $V_{CC} = 6V$, $V_{PP} = 12.5V$ and then set an address to first page address to be programmed. After data of 2 words are latched, these latch data are programmed simultaneously by applying 0.2 ms program pulse. Then a verify is performed. If each output data is not verified correctly, apply one more 0.2 ms program pulse. The programmer continues 0.2 ms pulse-then-verify routines until each output data is verified correctly or twenty five of these pulse-then-verify routines have been completed.

The programmer also maintains its total number of 0.2 ms pulse applied to that page addresses in register X. And then applied a program pulse X times of 0.2 ms width as an overprogram pulse. When the programming procedure above is finished, step to the next page address and repeat this procedure till last page address to be programmed. When the entire page addresses have been programmed completely, all addresses should be verified with $V_{CC} = V_{PP} = 5V$.

DC ELECTRICAL CHARACTERISTICS ($T_a = 25 \pm 5^\circ C$, $V_{CC} = 6V \pm 0.25V$, $V_{PP} = 12.5V \pm 0.3V$, unless otherwise noted)

Symbol	Parameter	Test condition	Limits			Unit
			Min	Typ	Max	
I_{LI}	Input current	$V_{IN} = 0V \sim V_{CC}$			10	μA
V_{OL}	Output low voltage	$I_{OL} = 2.1mA$			0.45	V
V_{OH}	Output high voltage	$I_{OH} = -400\mu A$	2.4			V
V_{IL}	Input low voltage		-0.1		0.8	V
V_{IH}	Input high voltage		2.0		V_{CC}	V
I_{CC}	V_{CC} supply current				50	mA
I_{PP}	V_{PP} supply current	$\overline{PGM} = V_{IL}$			100	mA

AC ELECTRICAL CHARACTERISTICS ($T_a = 25 \pm 5^\circ C$, $V_{CC} = 6V \pm 0.25V$, $V_{PP} = 12.5V \pm 0.3V$, unless otherwise noted)

Symbol	Parameter	Test condition	Limits			Unit
			Min	Typ	Max	
t_{AS}	Address setup time		2			μs
t_{OES}	\overline{OE} setup time		2			μs
t_{DS}	Data setup time		2			μs
t_{AH}	Address hold time		0			μs
t_{AHL}			2			μs
t_{DH}	Data hold time		2			μs
t_{DFP}	\overline{OE} to output float delay		0		130	ns
t_{VCS}	V_{CC} setup time		2			μs
t_{VPS}	V_{PP} setup time		2			μs
t_{PW}	PGM initial program pulse width		0.19	0.2	0.21	ms
t_{OPW}	PGM over program pulse width		0.19		5.25	ms
t_{CES}	\overline{CE} setup time		2			μs
t_{OE}	Data valid from \overline{OE}				150	ns
t_{LW}	Data latch time		1			μs
t_{PGMS}	PGM setup time		2			μs
t_{CEH}	\overline{CE} hold time		2			μs
t_{OEH}	\overline{OE} hold time		2			μs

Note 5: V_{CC} must be applied simultaneously V_{PP} and removed simultaneously V_{PP} .

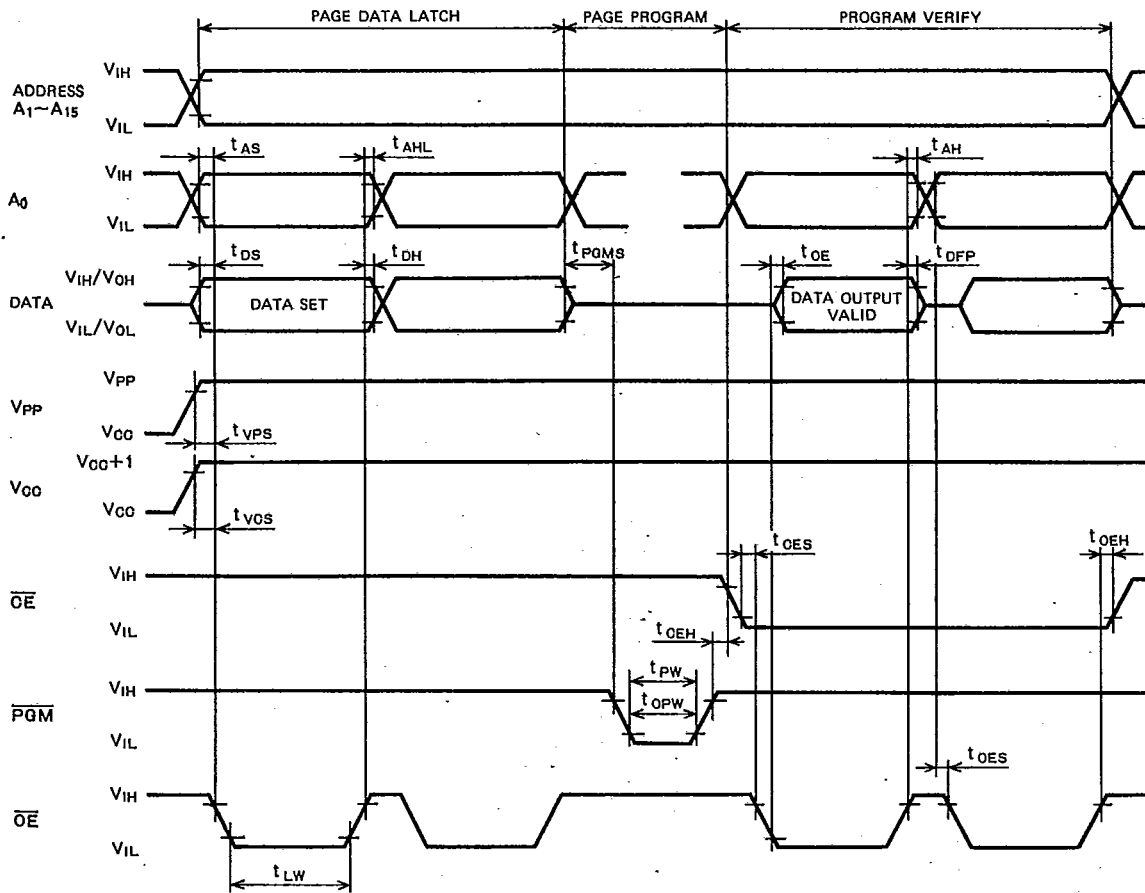
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AC WAVEFORMS



Test condition for A.C characteristics
 - Input voltage: V_{IL} = 0.45V, V_{IH} = 2.4V
 - Input rise and fall time: (10% ~ 90%): ≤ 20ns
 - Reference voltage at timing measurement: Input, Output "L" = 0.8V, "H" = 2V.